

5.3 Kontrolle rauschinduzierter Oszillationen in raum-zeitlichen Systemen

1. Halbleiter-Übergitter

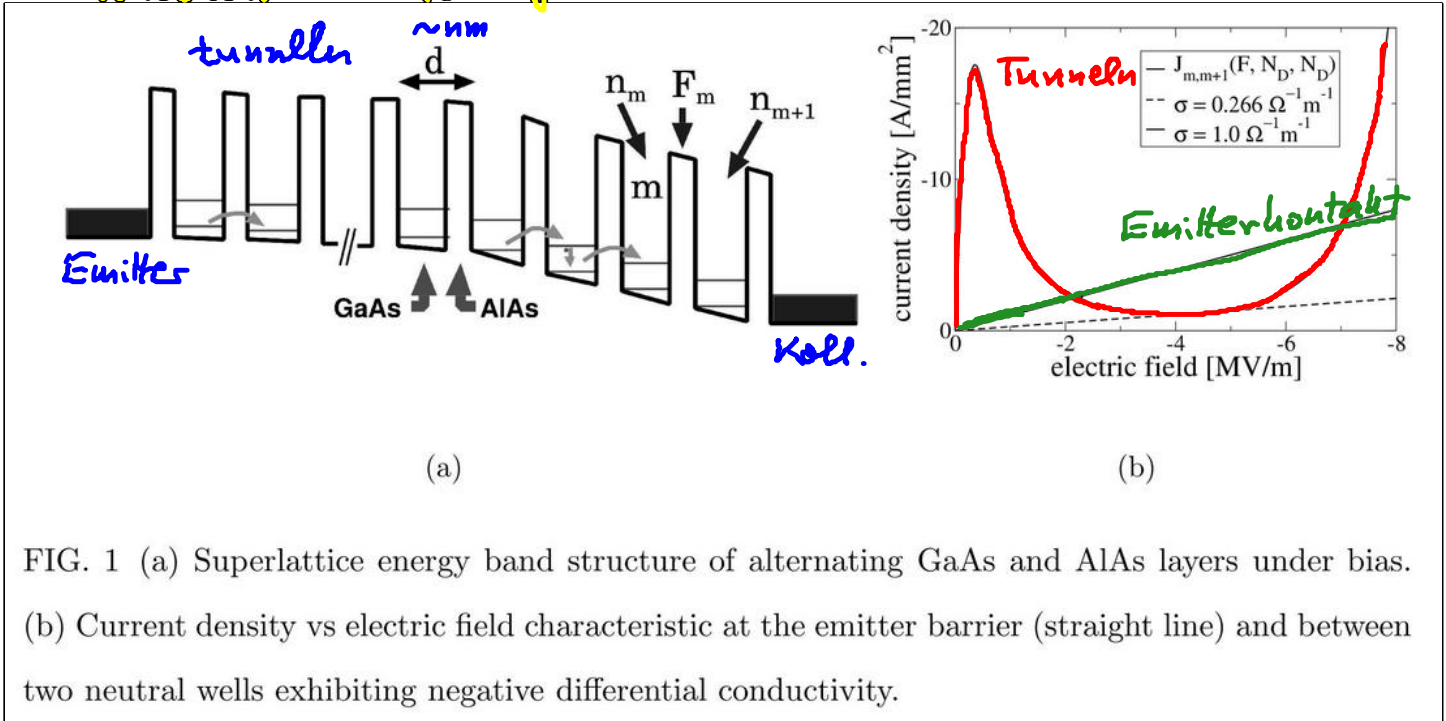


FIG. 1 (a) Superlattice energy band structure of alternating GaAs and AlAs layers under bias. (b) Current density vs electric field characteristic at the emitter barrier (straight line) and between two neutral wells exhibiting negative differential conductivity.

Hizaidis, Balanov, Amann, Schöll : PRL 96, 244104 (2006)

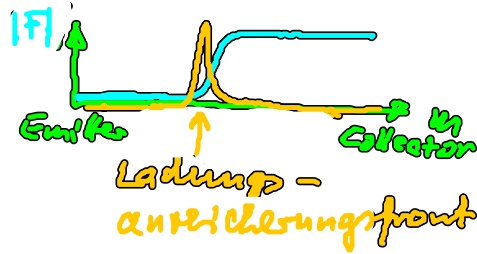
$$\epsilon \epsilon_0 (F_m - F_{m-1}) = e (n_m - N_D) \quad (m = 1, \dots, N) \quad \left(\begin{array}{l} \text{diskretes Gauß-Gesetz} \\ e < 0, \text{ Doping } N_D \end{array} \right)$$

$$e n_m = J_{m-1 \rightarrow m} + D \xi_m(t) - J_{m \rightarrow m+1} - D \xi_{m+1}(t)$$

(Ladungsträger-Kontinuitäts-gl. mit Gauss'schem weißen Rauschen $\langle \xi_m(t) \rangle = 0$, $\langle \xi_m(t) \xi_m(t') \rangle = \delta(t-t') \delta_{mm'}$)
 resonante Tunnelstromdiode J , shot noise, thermal noise

Anwendung: Hochfrequenzoszillator

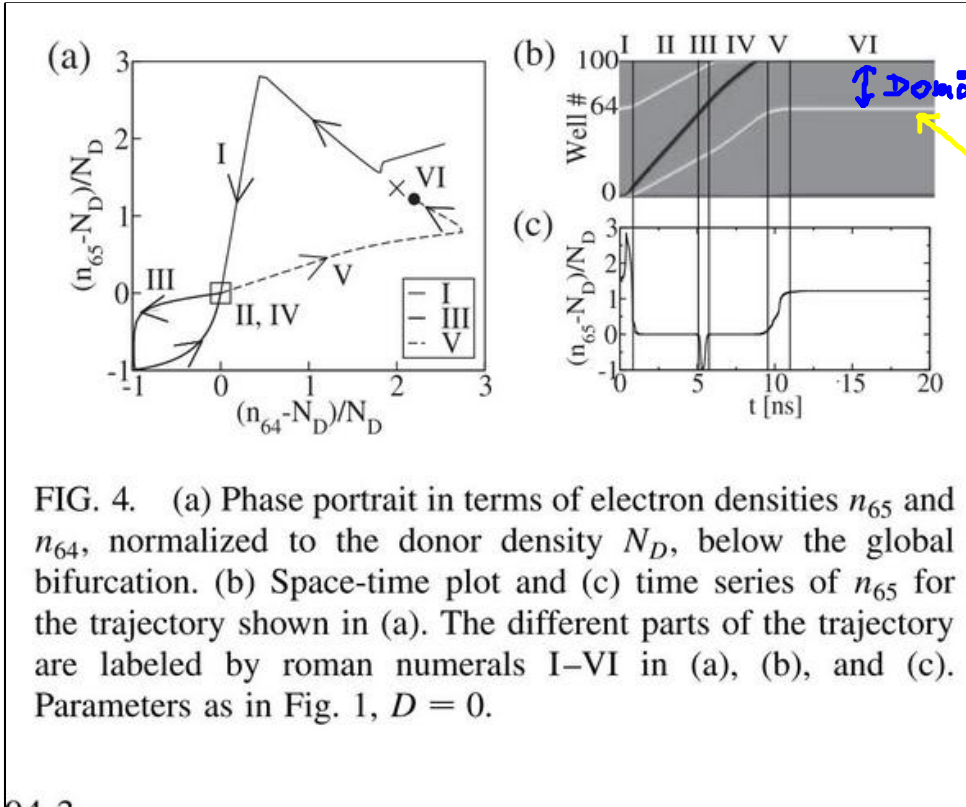
$D=0$: stationäre Felddomänen \rightarrow laufende Domänen



SNIPER-Exp.
(wie gener. Modell in 5.2)

globale Bedingung: Spannung
Ohm'sche Randbed. $J_{0 \rightarrow 1} = \sigma F_0$

$$U = - \sum_{n=0}^N F_n d$$



\downarrow Domäne
Anreicherungsfront

FIG. 4. (a) Phase portrait in terms of electron densities n_{65} and n_{64} , normalized to the donor density N_D , below the global bifurcation. (b) Space-time plot and (c) time series of n_{65} for the trajectory shown in (a). The different parts of the trajectory are labeled by roman numerals I–VI in (a), (b), and (c). Parameters as in Fig. 1, $D = 0$.

$D \neq 0$: rauschinduzierte Domänenbewegung

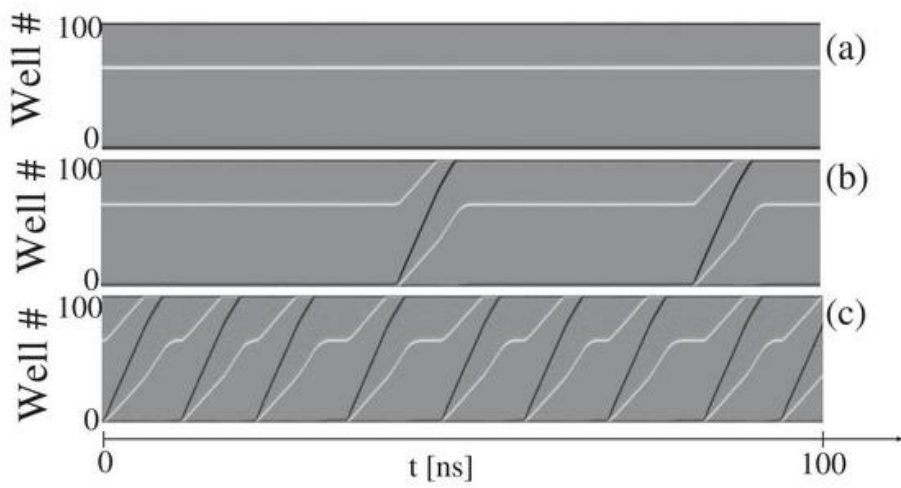


FIG. 1. Noise-induced front motion: Space-time plots of the electron density for (a) $D = 0$ (no noise), (b) $D = 0.5 \text{ A s}^{1/2}/\text{m}^2$, and (c) $D = 2.0 \text{ A s}^{1/2}/\text{m}^2$. Light and dark shading corresponds to electron accumulation and depletion fronts, respectively. The emitter is at the bottom. Parameters: $U = 2.99 \text{ V}$, $\sigma = 2.0821012488 \text{ } \Omega^{-1} \text{ m}^{-1}$, $N_D = 10^{11} \text{ cm}^{-2}$, $T = 20 \text{ K}$, $N = 100$ GaAs wells of width $w = 8 \text{ nm}$, and $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ barriers of width $b = 5 \text{ nm}$, energies $E^a = 41.5 \text{ meV}$, $E^b = 160 \text{ meV}$, scattering width $\Gamma = 8 \text{ meV}$, transition matrix elements $H_{m,m+1}^{a,b} = -eF_m \times 0.0127 \text{ m}$, $H_{m+1,m}^{a,a} = -0.688 \text{ meV}$, $H_{m+1,m}^{b,b} = 1.263 \text{ meV}$, as in Ref. [9].

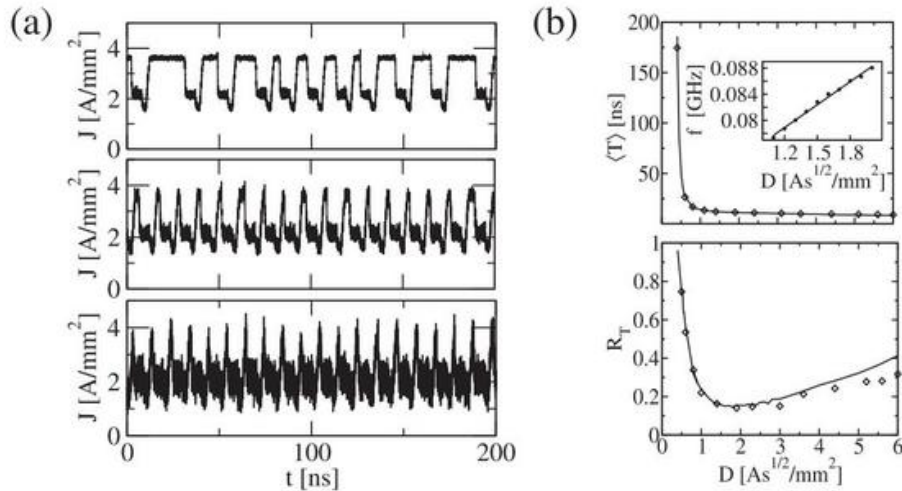
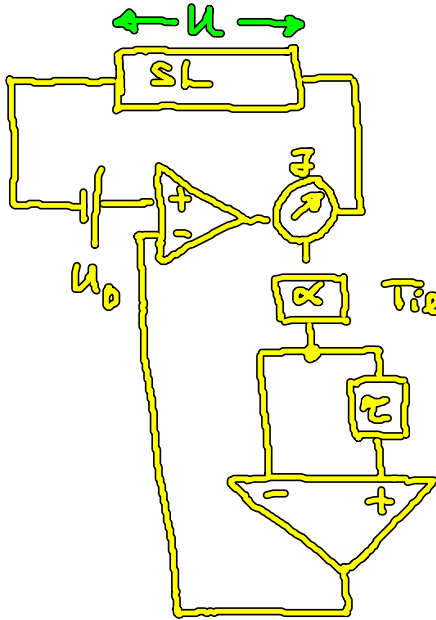


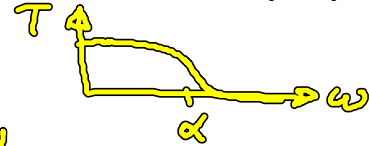
FIG. 2. (a) Three noise realizations of the current density $J(t)$. From top to bottom, $D = 0.8$, $D = 2.0$, and $D = 5.0 \text{ A s}^{1/2}/\text{m}^2$. (b) Mean interspike interval (top panel) and its normalized fluctuations R_T (bottom panel) versus noise intensity. Lines, constant D ; diamonds, $D \sim J_{m-1 \rightarrow m}^{1/2}$ [18]. The inset shows the peak frequency versus D .

Rückkopplungskontrolle



$$u = u_0 - K [\bar{j}(t) - \bar{j}(t-\tau)]$$

Tiefpassfilter $\bar{j} = \alpha \int_0^t j(t') e^{-\alpha(t-t')} dt'$
 (Abschneidefrequenz α)

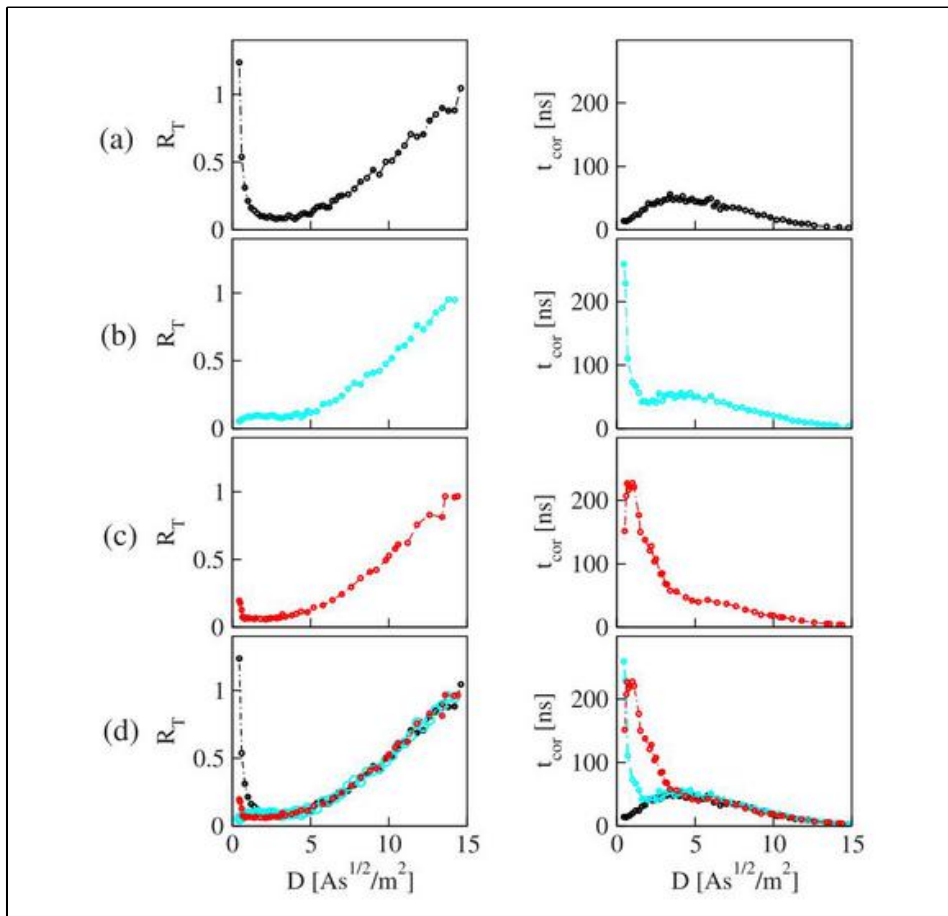


$$\bar{j} = \frac{1}{N+1} \sum_{n=0}^N j_{n \rightarrow n+1}$$

Gesamtstrom (incl. Verdünnungsstrom)

- Delay-induz. homokline Bif. zu lang. Domänen (wie im gener. SNIPER-Modell)
- Kontrolle der Kohärenzmonazie

Hizanidis & Schöll, PRE 78, 066205 (2008)



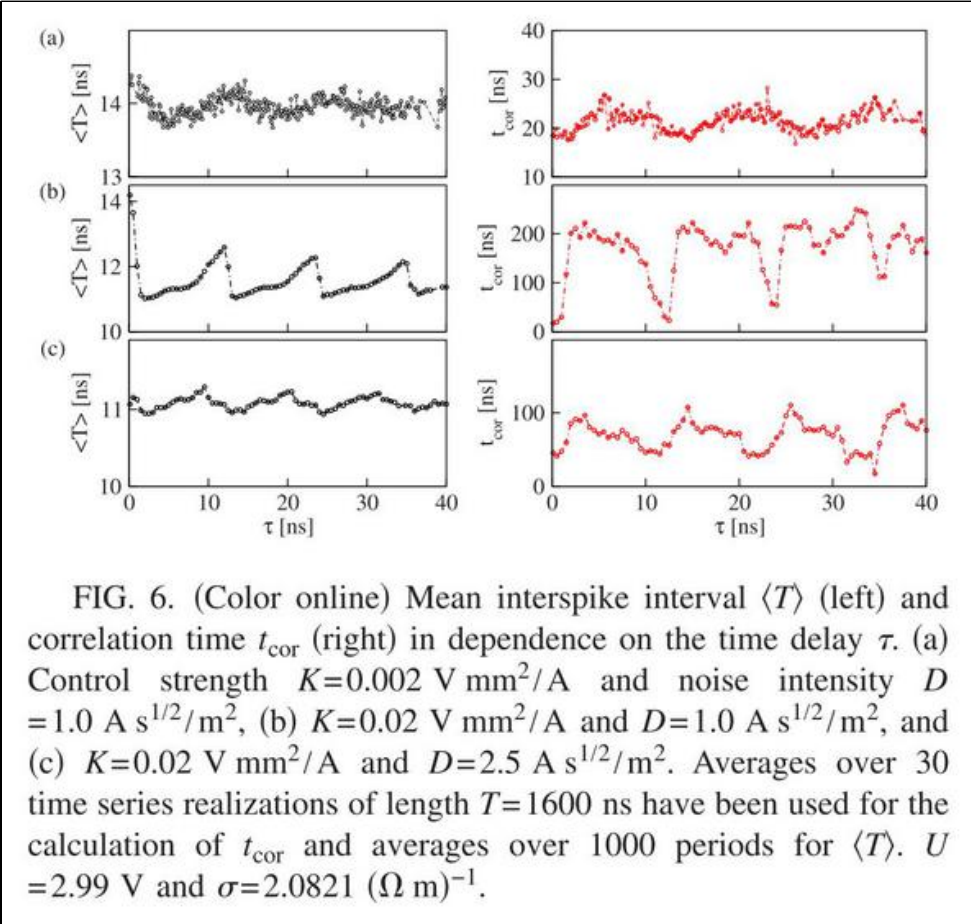
$K=0$

nichtopt. τ
 \rightarrow Kohärenzreson. zerstört

optimales τ
 \rightarrow Kohärenzreson. verstärkt

(beide im delay-induz. Res.-Regime)

FIG. 7. (Color online) Correlation time (right) and normalized fluctuation of pulse durations (left) as a function of the noise intensity for (a) $K=0$, (b) $(K, \tau)=(0.02 \text{ V mm}^2/\text{A}, 11 \text{ ns})$, and (c) $(K, \tau)=(0.02 \text{ V mm}^2/\text{A}, 14.5 \text{ ns})$. All three curves are plotted together in (d). Averages over 30 time series realizations of length $T=1600 \text{ ns}$ have been used for the calculation of t_{cor} and averages over 1000 periods for R_T . $U=2.99 \text{ V}$ and $\sigma=2.0821 (\Omega \text{ m})^{-1}$.



zu kleines K

kleine Rauschint.

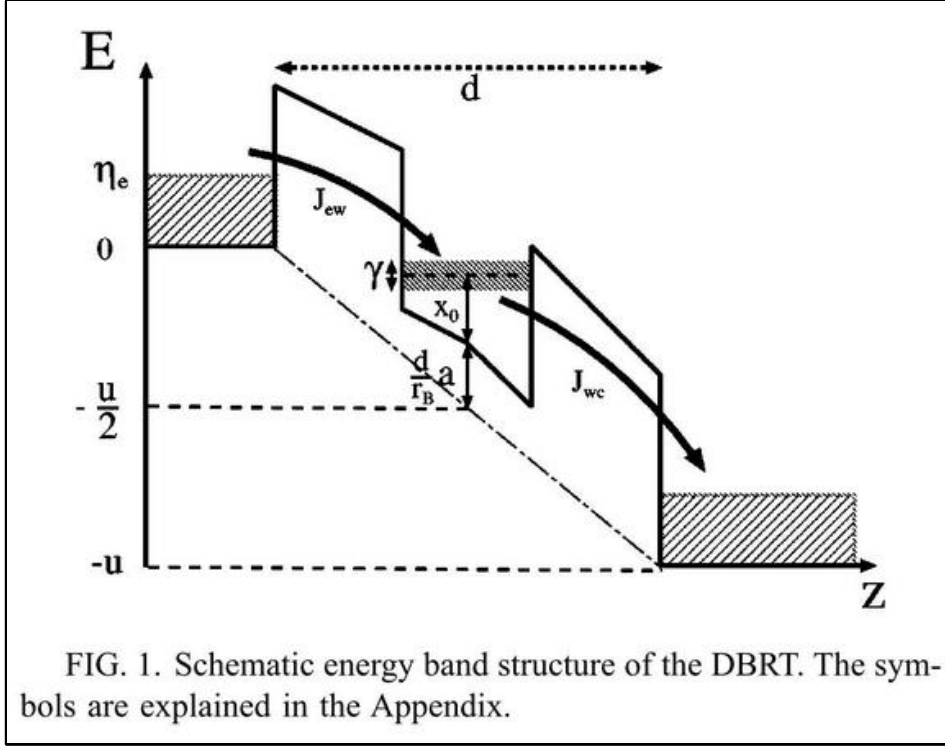
große Rauschint.

2. Resonante Tunneldiode

Stegenmann, Balanos, Schöll : PRC 71, 016221 (2005)

PRC 73, 016203 (2006)

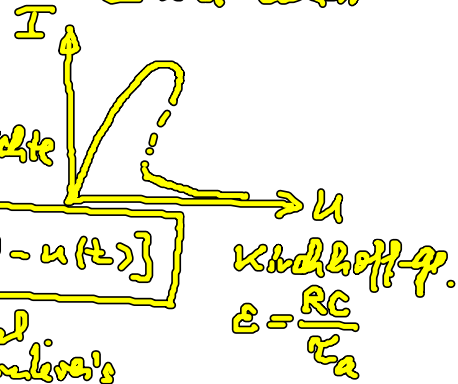
Mejer, Schöll : PRC 79, 011101 (2009)



Double Barrier Resonant Tunnel Diode (DBRT)

Bandverbiegung durch Lad.ansamml. in QW

⇒ Z-statt N-förmige I-U-Char



$$\dot{a} = f(a, u) + D \frac{d^2 a}{dx^2} + D_a \delta(x - x_0)$$

$$\dot{u} = \frac{1}{C} (U_0 - u - R J) + D_u \zeta(t) + K [u(t - \tau) - u(t)]$$

Reaktions-Diff.-Modell mit globaler Kopplung

Rückkoppl. über Shockley's

Kirkhoff-g.
 $C = \frac{RC}{\tau_a}$

- raum-zeitl. Osz. (breathing current filaments) durch Hopf-Bif. ($D=K=0$)
- knapp unterhalb der Hopf-Bif.: rauschinduz. breathing ($K=0$)

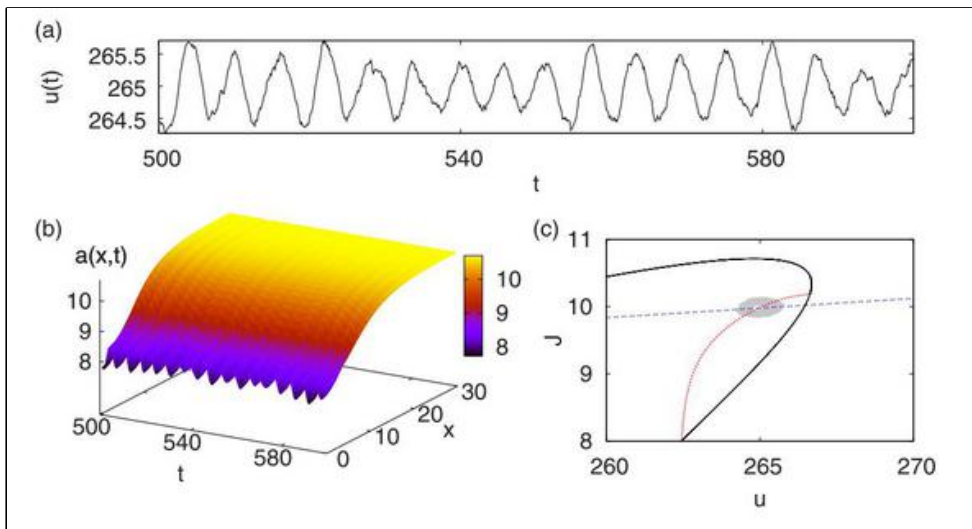
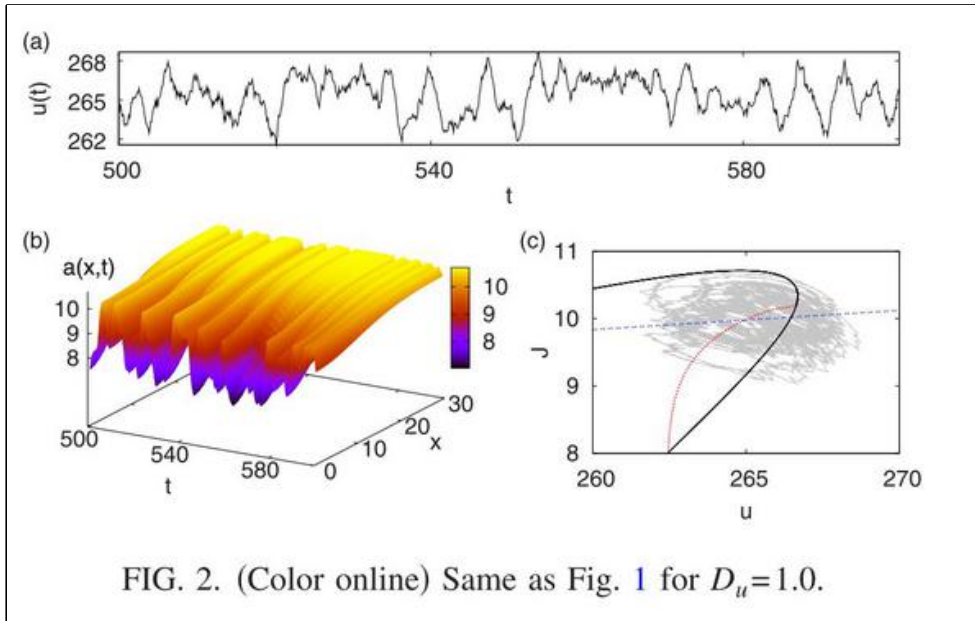


FIG. 1. (Color online) Stochastic spatiotemporal dynamics under multiple time-delayed feedback control. (a) Voltage time series $u(t)$ (in units of 0.35 mV), (b) charge carrier density $a(x, t)$ (in units of $10^{10}/\text{cm}^2$), (c) phase portrait of current J (in units of 500 A/cm²) vs voltage u . Space x and time t are scaled in units of 100 nm and

vs voltage u . Space x and time t are scaled in units of 100 nm and 3.3 ps, respectively, corresponding to typical device parameters at 4 K [29]. Parameters are $U_0 = -84.2895$, $r = -35$, $\varepsilon = 6.2$, $D_u = 0.1$, $D_a = 10^{-4}$, $K = 0.1$, $\tau = 6.3$, $R = 0.5$.



• Vergrößerung von t_{cor} \rightarrow τ durch opt. τ

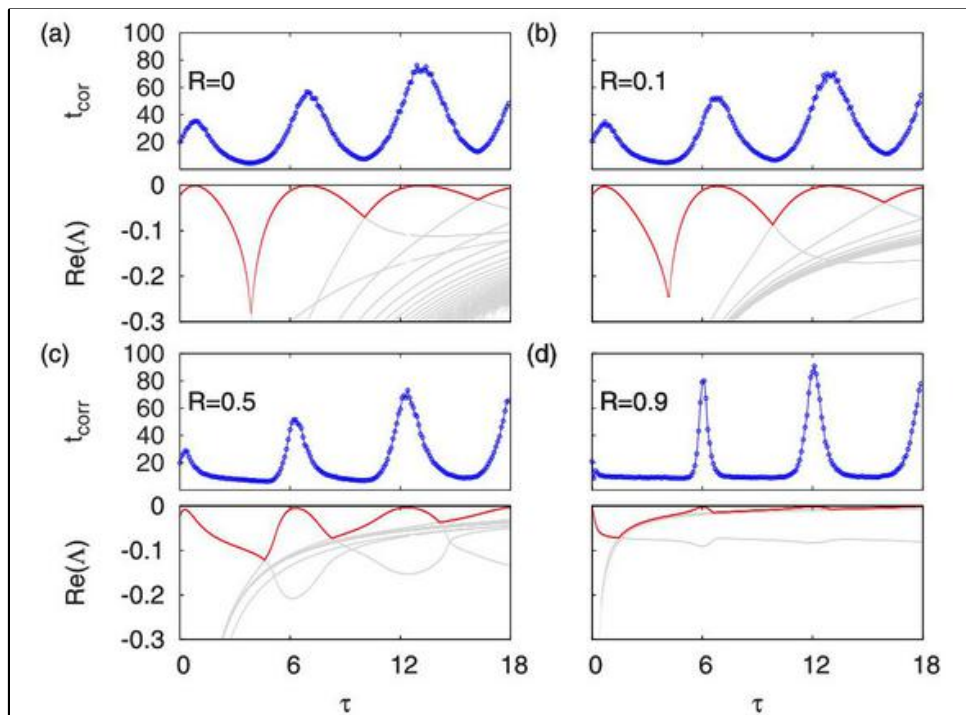


FIG. 7. (Color online) Correlation times t_{cor} (upper panels) and deterministic stability of the inhomogeneous fixed point, $\text{Re}(\Lambda)$ (lower panels), in dependence of the delay time τ for different values of the memory parameter R [(a)–(d)] and fixed $K = 0.1$. The red (dark) curves in the lower panels mark the leading eigenvalue, which governs the overall stability of the fixed point. Parameters: $\varepsilon = 6.2$, $D_u = 0.1$, and $D_a = 10^{-4}$ (in the panels showing t_{cor}).

6. Kontrolle in optischen Systemen

6.1 Laser & Kontrolle

6.2 Rauschunterdrückung im Laser

6.3 zeitverzögert gekoppelte Laser

6.1 Laser & Kontrolle

Beschreibung: semiklassische Gleichungen

- Elektrisches Feld: klassisch (Maxwell-Gleichungen)
- Atome: quantentheoretisch (Besetzungsinversion und ggf. Polarisation der Atome aus Schrödinger-Gleichung)

hier: adiabatische Eliminierung der Polarisation

$$\left(\frac{1}{\tau_{\text{pd}}} \gg \frac{1}{\tau_{\text{Feld}}} : \text{Polarisation folgt instantan} \right)$$

Lang-Kobayashi-Gleichungen:

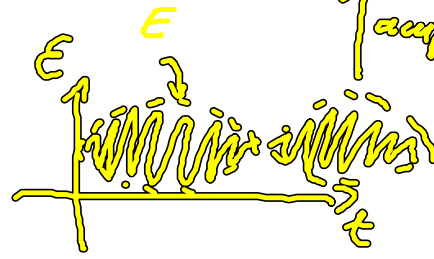
Ref.: R. Lang, K. Kobayashi, IEEE J. Quantum Electronics 16, 347 (1980)

$$\frac{dE}{dt} = \frac{1}{2} (1+i\alpha) n E - E_b + F_E$$

$$T \frac{dn}{dt} = I - n - (1+n) k(n) |E|^2$$

Variablen & Parameter:

E : Komplexes elektrisches Feld (slowly varying envelope approximation)



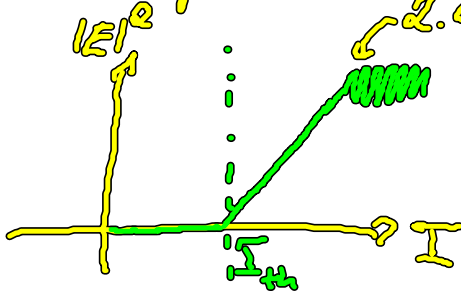
und $|E|^2$ Intensität

α : linewidth enhancement factor

n : Ladungsträgerdichte (Inversion relativ zur Laser-Schwelle bei $n_{th} \stackrel{!}{=} 0$)

T : Zeitskalenparameter $\frac{\tau_{carrier}}{\tau_{photon}} \approx 10^3$

I : Pumpstrom



2. Laser-Schwelle (für spezielle Laser)

\Rightarrow Intensitätsozillationen

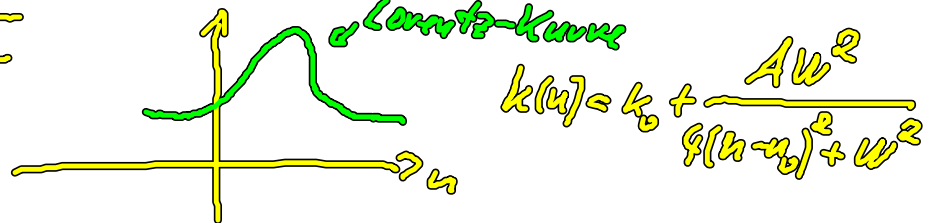
oberhalb einer Hopf-Bifurkation

in Gleichungen berücksichtigt durch

$k(n)$ (passives, internes feedback in Laser)

$k(n)$ mit "Bragg grating"

"Lorentz-Kurve"



$$k(n) = k_0 + \frac{A n^2}{1 + (n - n_0)^2 + n^2}$$

zusätzliche Einflüsse:

E_b : optisches feedback analog zu Pyragas-Kontrolle

$$E_b(t) = \kappa e^{i\varphi} \sum_{m=0}^{\infty} R^m [E(t - \delta - m\tau) - E(t - \delta - (m+1)\tau)]$$

F_E : Rauschterm (\rightarrow 6.2)

